EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	5	("20040145056" | "5050838" | "6020215" | "6162367" | "6706548").PN.	US-PGPUB; USPAT	ADJ	ON	2008/12/06 10:14
S2	16	((JOZEF) near2 ("VAN BEEK")).INV.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/06 10:15
S3	32	((JOZEF) near2 ("VAN BEEK")).INV.	EPO; JPO; DERWENT	ADJ	ON	2008/12/06 10:15
S4	5	((MATHIEU) near2 (ULENAERS)).INV.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/06 10:15
S5	5	((MATHIEU) near2 (ULENAERS)).INV.	EPO; JPO; DERWENT	ADJ	ON	2008/12/06 10:15
S6	11805	mems and fluori$3	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 13:11
S7	781	mems and (fluori$3 with layer with (remov$3 or etch$3 or sacrific$4))	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 13:12
S8	0	S7 and "257".ccls.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 13:12
S9	173	S7 and "257".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 13:12
S10	263	S7 and "438".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 13:13
S11	47	(S9 or S10) and (mem or mems).ti.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 13:16
S13	16702	mems.ti,ab.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:33
S14	189856	silicon substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:34
S16	509030	(insulat$3 or etch$5 or oxid$5) layer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:35
S17	457582	fluroine or fluoride or hf or hydrofluori$3	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:35

S18	2162	S13 and S14	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:36
S19	1030	S18 and S16	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:36
S20	468	S19 and S17	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:36
S21	9760	(fluroine or fluoride or hf or hydrofluori$3) same (dry near3 etch$3)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:37
S22	66	S13 AND S14 AND S16 and S21	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:37
S23	14009	(fluorine or fluoride or hf or hydrofluori$3) same (dry near3 etch$3)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:39
S24	73	S13 AND S14 AND S16 and S23	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:39
S25	1009	257/417.ccls.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 10:22
S26	132	(mem or mems) and S25	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 10:25
S27	121	S26 and substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 10:26
S28	1009	257/417.ccls.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 13:46
S29	132	(mem or mems) and S28	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 13:46
S30	83	S29 and silicon near3 substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 13:46
S31	83	S29 and (silicon near3 substrate)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 13:46

S32	30	("5015850" | "5210714" | "5226321" | "5265470" | "5313835" | "5354985" | "5475318" | "5659195" | "5665253" | "5666190" | "5747804" | "5883387" | "5894090" | "5929497" | "5994750" | "6075585" | "6091125" | "6092423" | "6174820" | "6211532" | "6229190" | "6296779" | "6337027").PN. OR ("6580138").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/08 14:12
S33	76947	((etch stop) or oxide) near4 layer near4 substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:15
S34	21291	S33 and metal oxide	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:15
S35	222251	hf$6	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:16
S36	11009	"hfo.sub.2"	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:16
S37	2254	S33 and S36	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:16
S38	85240	(mem or mems)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:17
S39	2572	S33 and S38	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:17
S40	677	S39 and metal oxide	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:17
S41	65	S39 and S36	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:17
S42	1	("6809394").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/08 14:19
S43	61	"al.sub.3O.sub.3"	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:22
S44	0	S43 and S39	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 14:22
S45	1010	257/417.ccls.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/09 09:31

S46	132	(mem or mems) and S45	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/09 09:31
S47	1	("20070222007").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/09 10:58
S48	1	("6621280").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/10 14:04
S49	14857	(silicon near3 substrate) and ("al.sub.2O.sub.3" or "HfO.sub.2" or "Zro.SUB.2" OR "T1O.sub.2")	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/23 09:44
S50	1222	S49 and etch stop	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/23 09:44
S51	2	(silicon near3 substrate) and (("al.sub.2O.sub.3" or "HfO.sub.2" or "Zro.SUB.2" OR "T1O.sub.2") near5 etch stop)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/23 09:50
S52	90	(silicon near3 substrate) and (("al.sub.2O.sub.3" or "HfO.sub.2" or "Zro.SUB.2" OR "T1O.sub.2") with etch stop)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/23 09:52
S53	3	(("20020031711") or ("20020117752") or ("20030003641")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/02/24 09:03
S54	90363	mem or (micro adj electromechanic$4)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 10:00
S55	90	(silicon near3 substrate) and (("al.sub.2O.sub.3" or "HfO.sub.2" or "Zro.SUB.2" OR "T1O.sub.2") with etch stop)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 10:00
S56	6	S54 and S55	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 10:00
S57	50802	sacrific$7 near3 (film or layer or substrate or material)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 14:08
S58	647	S57 and "439".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 14:10
S59	45	S58 and (mems or bistable adj switch or voltage adj switch)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 14:10
S60	201	(("al.sub.2O.sub.3" or "HfO.sub.2" or "Zro.SUB.2" OR "T1O.sub.2") with etch stop)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 14:11

S61	0	S58 and S60	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 14:11
S62	647	S57 and S58	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 14:11
S63	44	S57 and S60	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/02/24 14:11
S64	13	("2001/0005631").URPN.	USPAT	ADJ	ON	2009/02/24 14:14
S67	2	(etch$4 near2 stop) with ("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") and (MEMS or movable electrode)	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:28
S68	1420	("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") and (MEMS or movable electrode)	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:28
S69	248	(("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") with substrate) and (MEMS or movable electrode)	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:29
S70	10	(("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") with substrate) and (movable electrode)	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:32
S71	53	("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") and (movable electrode)	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:34
S72	43	S71 not S70	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:34
S73	13055	("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") and dielectric layer	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:40
S74	375	S73 and mems	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/08/31 14:41
S75	104	S74 and "438".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/08/31 14:41
S76	5373	("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") same dielectric layer	US-PGPUB; USPAT	ADJ	ON	2009/08/31 14:41
S77	107	S76 and mems	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/08/31 14:41
S78	0	(10/302349).APP.	USPAT; USOCR	ADJ	ON	2009/08/31 14:44
S79	1	("2003/0146463").URPN.	USPAT	ADJ	ON	2009/08/31 14:45

S80	5373	("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") same dielectric layer	US-PGPUB; USPAT	ADJ	ON	2009/08/31 16:55
S81	107	S80 and mems	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/08/31 16:55
S82	38	S81 and (etch near3 stop $4)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/08/31 16:55
S83	166	("hfo.sub.2" or "zro.sub.2" or "Tio.sub.2") with (etch near3 stop$4)	US-PGPUB; USPAT	ADJ	ON	2009/08/31 16:59
S84	3	((("5972722") or ("6211035") or ("20010055852")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/08/31 17:08
S85	12725	(fluorine or fluoride or hf) near4 plasma	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/12/15 06:23
S86	60902	(MEMS or movable electrode) and substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/12/15 06:23
S87	670	S85 and S86	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/12/15 06:23
S88	195	S87 and "438".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/12/15 06:23

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S89	6	((JOZEF) near2 ("VAN BEEK")).INV.	USPAT; UPAD	ADJ	ON	2009/12/15 06:17
S90	4	((MATHIEU) near2 (ULENAERS)).INV.	USPAT; UPAD	ADJ	ON	2009/12/15 06:17
S91	5457	(fluorine or fluoride or hf) near4 plasma	USPAT; UPAD	ADJ	ON	2009/12/15 06:19
S92	24073	(MEMS or movable electrode) and substrate	USPAT; UPAD	ADJ	ON	2009/12/15 06:20
S93	298	S91 and S92	USPAT; UPAD	ADJ	ON	2009/12/15 06:20
S94	103	S93 and "438".clas.	USPAT; UPAD	ADJ	ON	2009/12/15 06:21
S95	871	((fluorine or fluoride or hf) near4 plasma).clm.	USPAT; UPAD	ADJ	ON	2009/12/15 06:22
S96	1831	((MEMS or movable electrode) and substrate).clm.	USPAT; UPAD	ADJ	ON	2009/12/15 06:22

| S97 | 2 | S95 and S96 | USPAT; UPAD | ADJ | ON | 2009/12/15 06:22 |
| S98 | 34 | (((fluorine or fluoride or hf) near4 plasma) and etch stop).clm. | USPAT; UPAD | ADJ | ON | 2009/12/15 06:23 |

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